

N-channel 100 V 8.5 mΩ standard level MOSFET in TO220 17 October 2013 Product data sheet

## 1. General description

Standard level N-channel MOSFET in a TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

## 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

## 3. Applications

- AC-to-DC power supply equipment
- Motor control
- Server power supplies
- Synchronous rectification

## 4. Quick reference data

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	T <sub>j</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	263	W
Static charac	teristics		1				
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 13; Fig. 12		4.5	6.4	8.5	mΩ
Dynamic cha	racteristics		1				
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V;		-	33	-	nC
Q <sub>G(tot)</sub>	total gate charge	<u>Fig. 14; Fig. 15</u>		-	111	-	nC
Avalanche Ru	uggedness		1				
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS}$ = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 100 A; V <sub>sup</sub> ≤ 100 V; R <sub>GS</sub> = 50 Ω; unclamped; Fig. 3		-	-	219	mJ

[1] Continious current limited by package.

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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain	$2 \circ 4$	
3	S	source		G - UF A
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78)	

## 6. Ordering information

Table 3. Ordering information							
Type number	Package	Package					
	Name	Description	Version				
PSMN8R5-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN8R5-100PS	PSMN8R5-100PS

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	100	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>		-	75	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 4		-	429	А

PSMN8R5-100PS

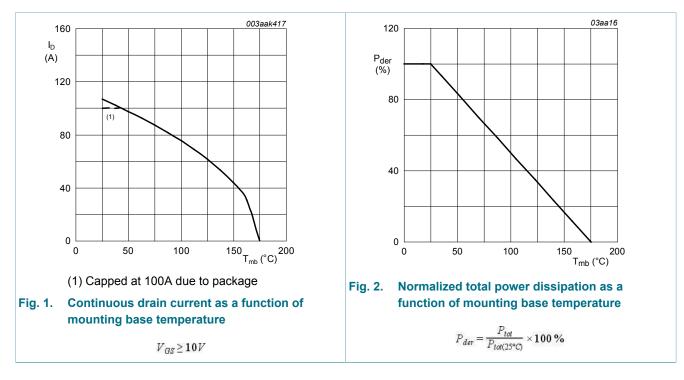
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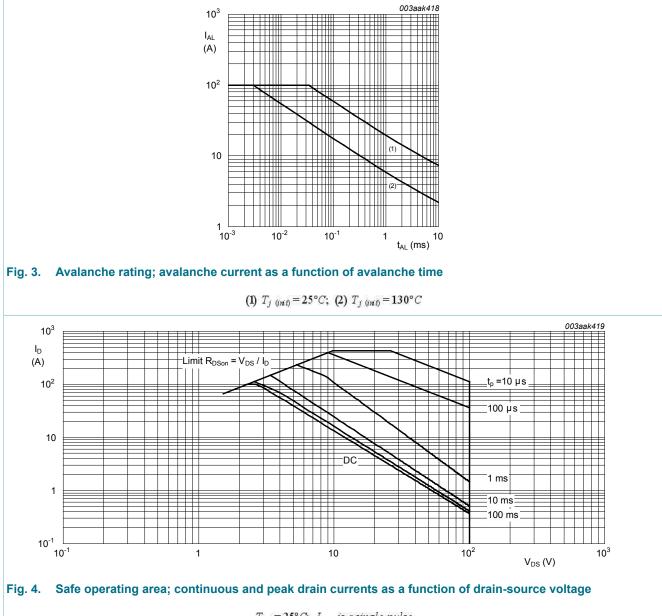
Symbol	Parameter	Conditions		Min	Мах	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	263	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drai	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	429	А
Avalanche I	Ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le 100$ V; $R_{GS}$ = 50 Ω; unclamped; Fig. 3		-	219	mJ



[1] Continious current limited by package.

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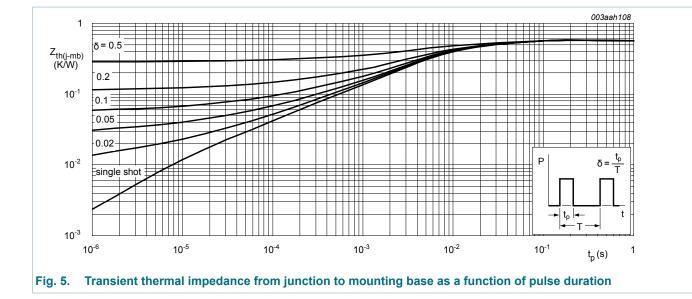


 $T_{mb} = 25^{\circ}C; \ I_{DM}$  is a single pulse

## 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	0.49	0.57	K/W

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## **10. Characteristics**

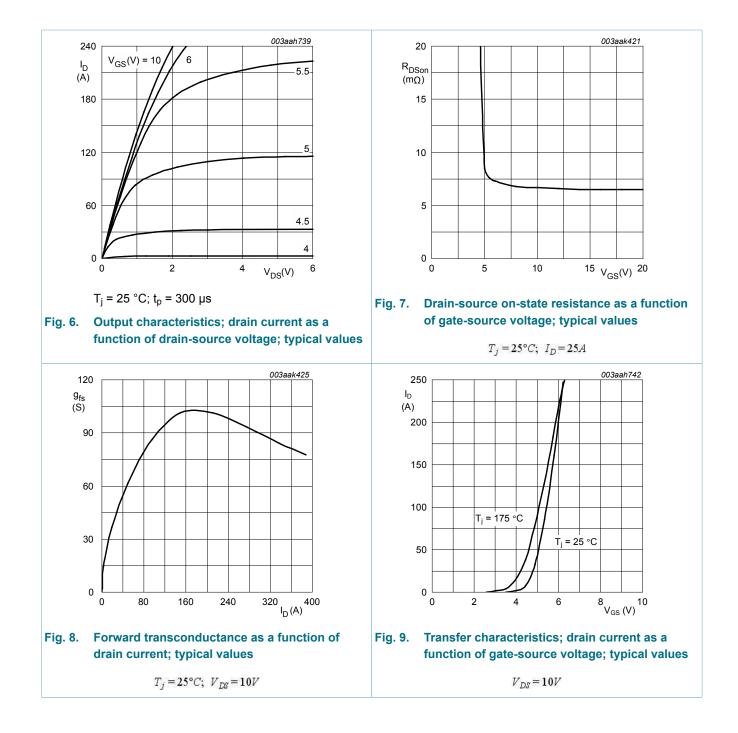
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	Т				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
breakdown voltage	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	2.4	3	4	V
V <sub>GSth</sub> gate-source voltage	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	1	μA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 100 °C	-	-	20	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12	-	16.95	22.6	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 12	-	11.18	14.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 13; Fig. 12	4.5	6.4	8.5	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	0.36	0.71	1.42	Ω

PSMN8R5-100PS	
PSIVINGR5-100P5	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V;	-	111	-	nC
Q <sub>GS</sub>	gate-source charge	<u>Fig. 14; Fig. 15</u>	-	24	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge		-	16	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	8	-	nC
Q <sub>GD</sub>	gate-drain charge		-	33	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 50 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	4.4	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$ T <sub>j</sub> = 25 °C; <u>Fig. 16; Fig. 17</u>	-	5512	-	pF
C <sub>oss</sub>	output capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$ T <sub>j</sub> = 25 °C; <u>Fig. 17</u>	-	380	-	pF
C <sub>rss</sub>	reverse transfer capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$ T <sub>j</sub> = 25 °C; <u>Fig. 16</u> ; <u>Fig. 17</u>	-	256	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 50 V; $R_{L}$ = 2 $\Omega$ ; $V_{GS}$ = 10 V;	-	20	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	35	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	87	-	ns
t <sub>f</sub>	fall time		-	43	-	ns
Source-drai	in diode					
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 18</u>	-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	53	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 50 V	-	124	-	nC

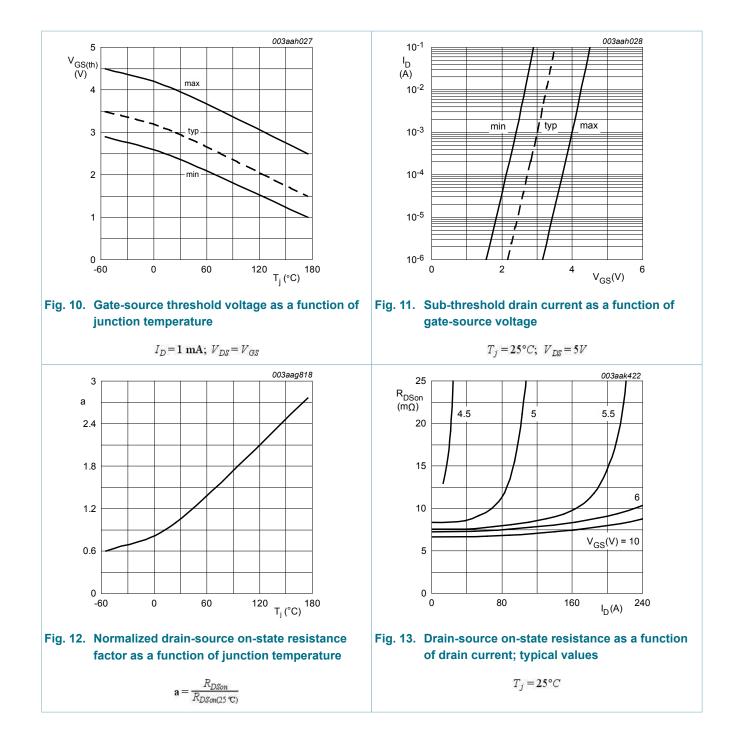
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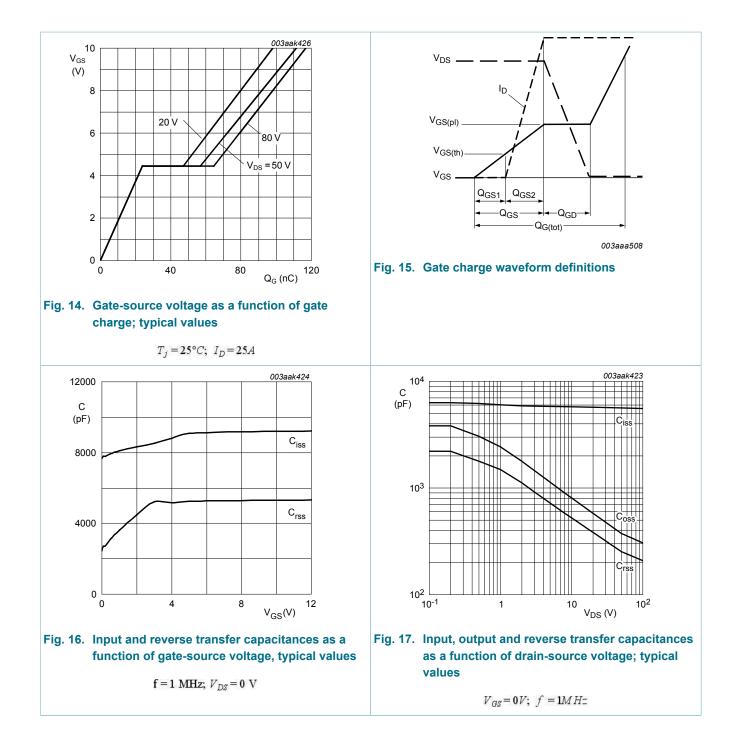
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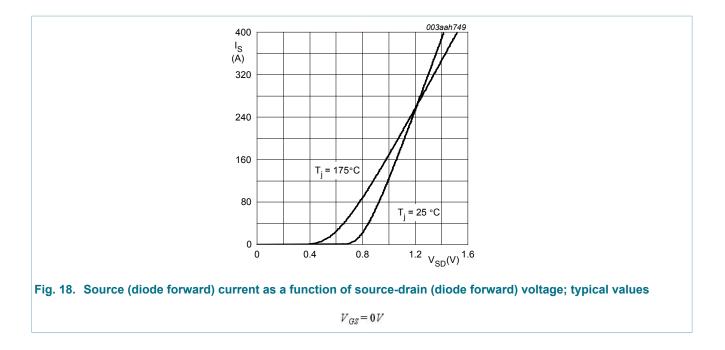
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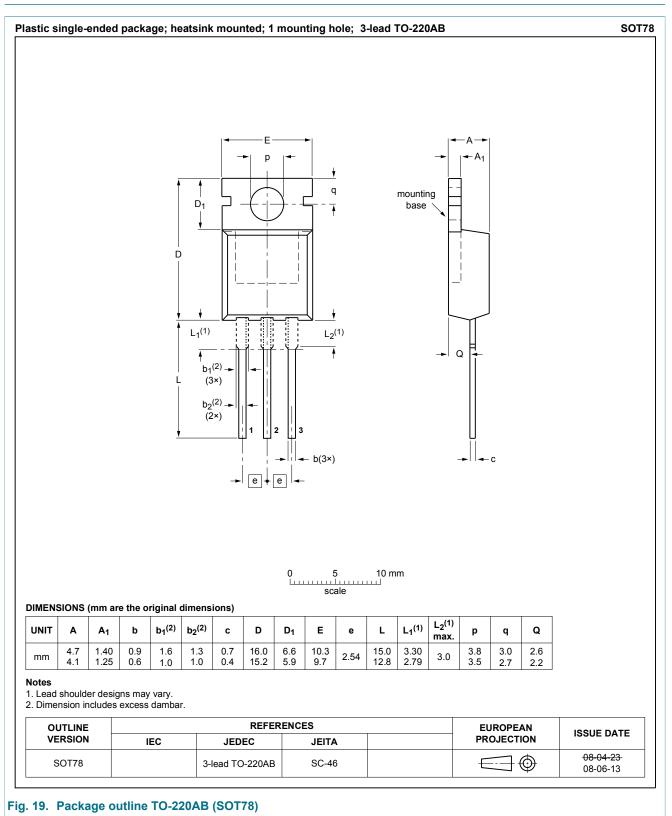
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## 11. Package outline



#### PSMN8R5-100PS

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